



The  
University  
Of  
Sheffield.

## DEPARTMENT OF ELECTRONIC AND ELECTRICAL ENGINEERING

Spring Semester 2006-2007 (2 hours)

### Introduction to VLSI Design 3

Answer **THREE** questions. **No marks will be awarded for solutions to a fourth question.** Solutions will be considered in the order that they are presented in the answer book. Trial answers will be ignored if they are clearly crossed out. **The numbers given after each section of a question indicate the relative weighting of that section.**

1.    a.    i.    Design a standard-CMOS, transistor-level circuit for an XOR function of two inputs,  $A$  and  $B$  (hint:  $Y = A \oplus B = A.\bar{B} + \bar{A}.B$ ) and size the transistors for a minimum sized gate. (8)
  - ii.    How would you change the circuit in part **1.a.i** to produce an XNOR function. (2)
  - b.    i.    Draw a circuit diagram to show how a two input XOR function could be implemented using two transmission gates (TG) and a few inverters. (6)
  - ii.    How, optimally, would the circuit in part **1.b.i** be changed to produce an XNOR function? (1)
  - iii.    Does the TG approach to implementation have any advantages or disadvantages over the standard-CMOS approach? If so, what are they? (3)
2.    The circuit in **Figure 2** (which is somewhere inside an IC and part of a bigger circuit) must be altered to allow it to be tested.

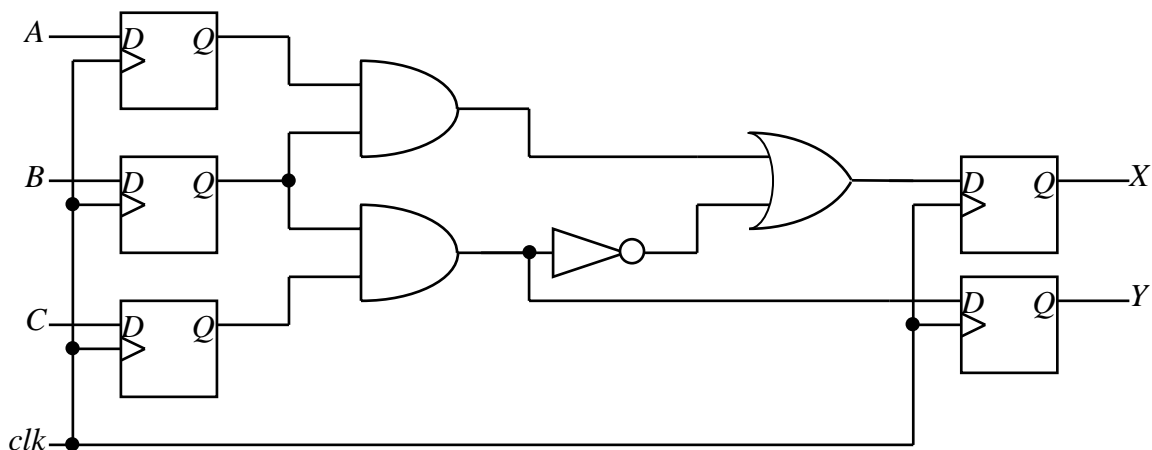
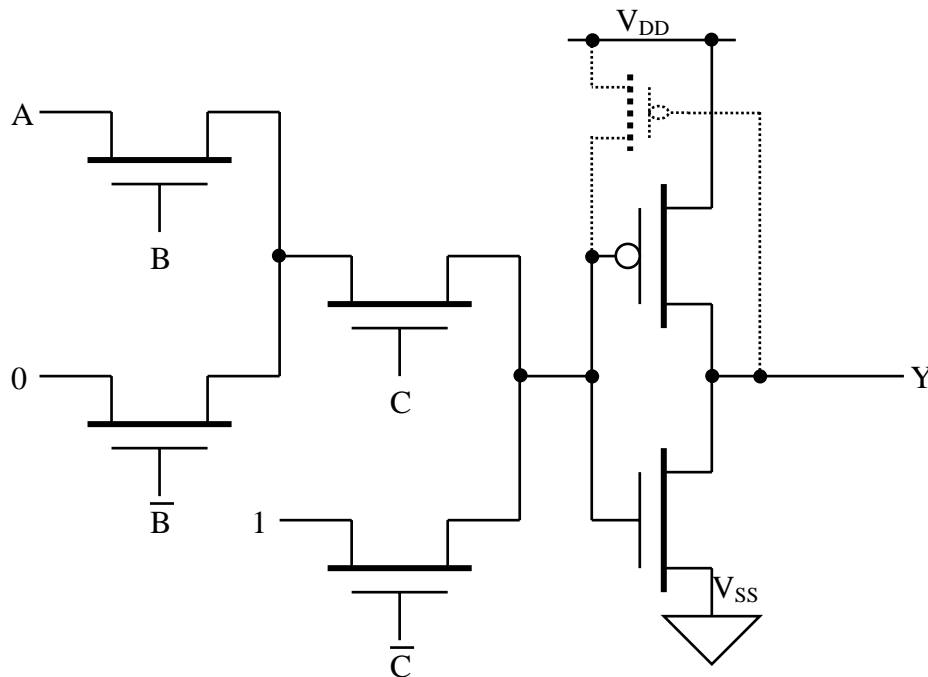


Figure 2

- a.
    - i. What changes must be made to the circuit to allow it to be tested (draw a diagram to show what must be done)? (4)
    - ii. Assuming a simple stuck-at fault model, identify how many individual tests must be applied and the associated test vectors. (8)
    - iii. Are there any problems with testing this particular part of the circuit? (2)
  - b. What is BIST and how is it used? What is the significance of the *signature*? (4)
- How is communication normally made between the outside of an IC and the test structures inside the IC? (2)
- 3. A  $0.13\mu\text{m}$  digital IC can be modelled as being equivalent to  $15 \times 10^6$  simple, 2-input gates where each gate has, on average, the equivalent of  $35\mu\text{m}$  of wire connected to its output. Each gate has an input capacitance of  $3\text{fF}$  on each input and an effective output capacitance of  $1.5\text{fF}$ . The wiring, on average, has a capacitance equivalent to  $0.2\text{fF}/\mu\text{m}$ .  
 The IC is clocked at  $2\text{GHz}$  with a power supply voltage of  $1.8\text{V}$  and, on average, the probability of any wire changing state on the rising edge of the clock is  $0.15$ .
  - a. Derive an expression for the power dissipation in a digital CMOS circuit due to switched capacitance. (4)
  - b.
    - i. What is the total capacitance that is being switched in the IC? (2)
    - ii. What is the power dissipation of the IC, due to switched capacitance, under the stated conditions? (4)
  - c.
    - i. What is other major contributor to the overall dynamic power dissipation apart from switched capacitance? (2)
    - ii. What factors give rise to static power dissipation – what is happening to static power dissipation as the technology is shrunk? (4)
  - d. The technology that is used to fabricate the IC is shrunk to  $90\text{nm}$  (so that linear dimensions reduce by a factor of  $1.4$ ). Estimate, simply, what *might* happen to the power dissipation due to switched capacitance, stating any assumptions that you make. (4)

4. The circuit in **Figure 4** implements a logic function but is not implemented as a standard CMOS circuit.



### Figure 4

- a. What is the logical function of the circuit (*Hint: you can ignore the dotted transistor when determining the function*)? (8)
- b. Why do you think that the dotted transistor (shown smaller here to denote that it is a *weak* transistor – reduced current drive) is included in the circuit – make sure you describe its purpose? (4)  
Why is a *weak* transistor needed as opposed to a transistor of normal drive strength? (4)  
How would you make a *weak* transistor? (2)
- c. In the circuit in Figure 4 there are more *n*-type than *p*-type transistors. Does this make any difference to circuit layout? (2)

**NLS / MB**